

IN THE SPECIFICATION:

Please replace paragraph [029] with the following:

[029] A preferred material in the methods of the present invention is boron phosphorus silicate glass (BPSG) for an insulation layer in which a contact hole is provided. The insulation layer may also be composed of TEOS, doped silicon dioxide, BPSG, PSG, BSG, and silicon nitride, where TEOS is an oxide of silicon deposited in a chemical vapor deposition (CVD) process using a tetraethylorthosilicate precursor. The insulation layer is preferably situated on a semiconductor substrate of a semiconductor wafer. Other materials are dielectrics known in the art that are structurally sound so as to withstand processing conditions and field operating conditions. The dielectrics include, but are not limited to, oxides, nitrides, carbides, carbon nitrides, oxynitrides, ~~doped or slightly doped monocrystalline or polycrystalline silicon,~~ and equivalents.